

<b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)				Attorney Docket No.: 041514-5289		Application No.: 10/823,575	
<b>PTO Form-1449</b>				<b>PAGE 1 OF 1</b>			
				Applicant(s): Tadataka EDAMURA et al.			
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<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Sub Class	Filing Date
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Sub Class	<div style="display: flex; justify-content: space-between;"> <span>Translation Yes</span> <span>No</span> </div>
cn		JP 2002-257629	September 11, 2002	Japan			Abstract
cn		JP 07-036064	February 7, 1995	Japan			Abstract
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
cn	Gupta et al.; "Ultrafast Carrier Dynamics in III-V Semiconductors Grown by Molecular-Beam Epitaxy at Very Low Substrate Temperatures"; IEEE Journal of Quantum Electronics; Vol. 28; No. 10; pp. 2464-2472; (1982).						
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cn	Ogawa et al., "GaAs Ultrafast Photoconductive Switches and Their Application to Ultrafast Photonic Sampling Technology"; Appl. Phys. Letter, Vol. 66, (1995), pp. 2-12.						
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